



Microcrystalline Silicon Carbide for Silicon Heterojunction Solar Cells

Manuel Bernhard Pomaska

Forschungszentrum Jülich GmbH
Institute of Energy and Climate Research
IEK-5 Photovoltaics

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Schriften des Forschungszentrums Jülich
Reihe Energie & Umwelt / Energy & Environment

Band / Volume 392

ISSN 1866-1793

ISBN 978-3-95806-267-2

Contents

Abstract	3
Zusammenfassung	7
1. Introduction	11
2. Fundamentals	17
2.1. Working principles of solar cells	17
2.2. Passivated contacts	21
2.3. Window layer materials for SHJ solar cells	26
2.4. Microcrystalline silicon carbide	29
3. Experimental details	33
3.1. Preparation of microcrystalline silicon carbide	33
3.2. Preparation of silicon wafer and thin films	35
3.3. Characterization of structural properties	36
3.4. Characterization of opto-electronic properties	38
3.5. Characterization of passivation and solar cell	39
4. Material properties of microcrystalline silicon carbide	43
4.1. Unintentionally doped films	43
4.1.1. Influence of deposition parameters on microstructure	44
4.1.2. Stoichiometry and hydrogen content	50
4.1.3. Electrical conductivity	56
4.1.4. Optical absorption coefficient	63
4.2. Role of oxygen and nitrogen in the films	67
4.2.1. Atmospheric residuals	68

Contents

4.2.2. Heater temperature	71
4.2.3. Controlled oxygen incorporation	72
4.2.4. Controlled nitrogen incorporation	75
4.2.5. Model for electrical transport	75
4.2.6. Electrical conductivity beyond state-of-the-art	83
4.2.7. Optical absorption coefficient	84
5. Silicon carbide in silicon heterojunction solar cells	87
5.1. Silicon carbide in a-SiO _x :H(i) passivated SHJ solar cells	87
5.1.1. Effect of silicon carbide deposition on a-SiO _x :H(i) passivation .	88
5.1.2. SHJ solar cells with silicon carbide n-doped layer and a-SiO _x :H(i) passivation layer	96
5.2. Silicon carbide in SiO ₂ passivated SHJ solar cells	102
5.2.1. Effect of silicon carbide deposition on SiO ₂ passivation	103
5.2.2. SHJ solar cells with silicon carbide n-doped layer and SiO ₂ passivation layer	112
6. Conclusion and Outlook	123
A. Abbreviations and Symbols	127
B. List of publications	133
C. Curriculum Vitae	135
References	148
Acknowledgments	149

**Energie & Umwelt /
Energy & Environment
Band / Volume 392
ISBN 978-3-95806-267-2**

